风光欣技术资料

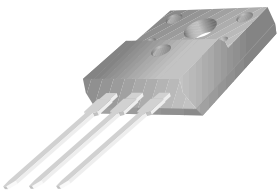
NPN TRANSISTORS D2137

■■ **APPLICATION：POWER AMPLIFIER APPLICATION.**

■■ **MAXIMUM RATING**（Ta=25℃）

PARAMETER		SYMBOL	RATING	UNIT
Collector-base voltage		V_{CBO}	60	V
Collector-emitter voltage		V_{CEO}	60	V
Emitter-base voltage		V_{EBO}	6	V
Collector current	D.C.	I_C	3	A
	Pulse	I_{CP}	5	A
Collector Power Dissipation	Ta=25℃	Pc	2	W
	Tc=25℃		10	
Junction Temperature		Tj	150	℃
Storage Temperature Range		Tstg	-55-150	℃

TO-220F



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1.Base 2.Collector 3.Emitter

■■**ELECTRICAL CHARACTERISTICS（Ta=25℃）**

PARAMETER	SYMBOL	TEST CONDITION	RATING			UNIT
			MIN.	TYP.	MAX.	
Collectoe-Base Breakdown Voltage	BVcbo	Ic=50uA ,Ie=0	60			V
Collector-Emitter Breakdown Voltage	BVceo	Ic=1 mA ,Ib=0	60			V
Emitter-Base Breakdown Voltage	BVebo	Ie=50uA ,Ic=0	6			V
Collector Cut-off Current	Iceo	Vcb=30 V ,Ie=0			0.1	uA
Collector-Emitter Cut-off Current	Ices	Vcb=60 V ,Vbe=0			0.1	uA
Emitter Cut-off Current	Iebo	Vcb=6V ,Ic=0			0.1	uA
Collector-Emitter Saturation Voltage	Vce(sat)	Ic=3A ,Ib=0.375A			1.2	V
DC Current Gain	H_{FE}	Vce=4V,Ic=1A	70		250	β
Gain bandwidth product	f_T	Vce=5V, Ic=0.2A, f=10MHz		30		MHz

■■h_{FE} **Classification And Marking**

Mark	D2137	
Classification	Q	P
h_{FE}	70~150	120~250